

## BC237/238/239

### **Switching and Amplifier Applications**

• Low Noise: BC239



# **NPN Epitaxial Silicon Transistor**

1. Collector 2. Base 3. Emitter

### **Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

| Symbol           | Parame                    | eter                   | Value     | Units  |
|------------------|---------------------------|------------------------|-----------|--------|
| V <sub>CES</sub> | Collector-Emitter Voltage | : BC237<br>: BC238/239 | 50<br>30  | V<br>V |
| V <sub>CEO</sub> | Collector-Emitter Voltage | : BC237<br>: BC238/239 | 45<br>25  | V<br>V |
| V <sub>EBO</sub> | Emitter-Base Voltage      | : BC237<br>: BC238/239 | 6<br>5    | V<br>V |
| I <sub>C</sub>   | Collector Current (DC)    |                        | 100       | mA     |
| P <sub>C</sub>   | Collector Dissipation     |                        | 500       | mW     |
| TJ               | Junction Temperature      |                        | 150       | °C     |
| T <sub>STG</sub> | Storage Temperature       |                        | -55 ~ 150 | °C     |

# $\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \text{unless otherwise noted}$

| Symbol                | Parameter                            | Test Condition                                       | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|--|------|------|------|-------|
| BV <sub>CEO</sub>     | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> =2mA, I <sub>B</sub> =0               |      |      |      |       |
|                       | : BC237                              |  | 45   |      |      | V     |
|                       | : BC238/239                          |  | 25   |      |      | V     |
| BV <sub>EBO</sub>     | Emitter Base Breakdown Voltage       | I <sub>E</sub> =1μA, I <sub>C</sub> =0               |      |      |      |       |
|                       | : BC237                              |  | 6    |      |      | V     |
|                       | : BC238/239                          |  | 5    |      |      | V     |
| I <sub>CES</sub>      | Collector Cut-off Current            |  |      |      |      |       |
|                       | : BC237                              | $V_{CE}=50V$ , $V_{BE}=0$                            |      | 0.2  | 15   | nA    |
|                       | : BC238/239                          | V <sub>CE</sub> =30V, V <sub>BE</sub> =0             |      | 0.2  | 15   | nA    |
| h <sub>FE</sub>       | DC Current Gain                      | V <sub>CE</sub> =5V, I <sub>C</sub> =2mA             | 120  |      | 800  |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA          |      | 0.07 | 0.2  | V     |
|                       |                                      | I <sub>C</sub> =100mA, I <sub>B</sub> =5mA           |      | 0.2  | 0.6  | V     |
| V <sub>BE</sub> (sat) | Collector-Base Saturation Voltage    | I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA          |      | 0.73 | 0.83 | V     |
|                       |                                      | I <sub>C</sub> =100mA, I <sub>B</sub> =5mA           |      | 0.87 | 1.05 | V     |
| V <sub>BE</sub> (on)  | Base-Emitter On Voltage              | V <sub>CE</sub> =5V, I <sub>C</sub> =2mA             | 0.55 | 0.62 | 0.7  | V     |
| f <sub>T</sub>        | Current Gain Bandwidth Product       | V <sub>CE</sub> =3V, I <sub>C</sub> =0.5mA, f=100MHz |      | 85   |      | MHz   |
|                       |                                      | V <sub>CE</sub> =5V, I <sub>C</sub> =10mA, f=100MHz  | 150  | 250  |      | MHz   |
| C <sub>ob</sub>       | Output Capacitance                   | V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz      |      | 3.5  | 6    | pF    |
| C <sub>ib</sub>       | Input Base Capacitance               | V <sub>EB</sub> =0.5V, I <sub>C</sub> =0, f=1MHz     |      | 8    |      | pF    |
| NF                    | Noise Figure                         | V <sub>CE</sub> =5V, I <sub>C</sub> =0.2mA,          |      |      |      |       |
|                       | : BC237/238                          | f=1KHz R <sub>G</sub> =2KΩ                           |      | 2    | 10   | dB    |
|                       | : BC239                              | $V_{CE}$ =5V, $I_{C}$ =0.2mA                         |      |      | 4    | dB    |
|                       | : BC239                              | $R_G=2K\Omega$ , $f=30\sim15KHz$                     |      |      | 4    | dB    |

## **h**<sub>FE</sub> Classification

| Classification  | А         | В         | С         |
|-----------------|-----------|-----------|-----------|
| h <sub>FE</sub> | 120 ~ 220 | 180 ~ 460 | 380 ~ 800 |

# **Typical Characteristics**

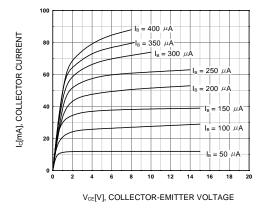


Figure 1. Static Characteristic

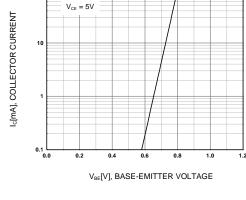


Figure 2. Transfer Characteristic

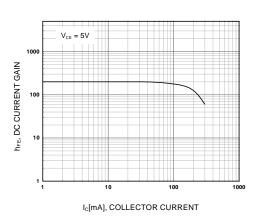


Figure 3. DC current Gain

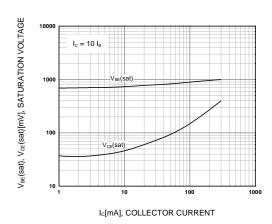


Figure 4. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

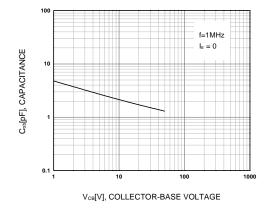


Figure 5. Output Capacitance

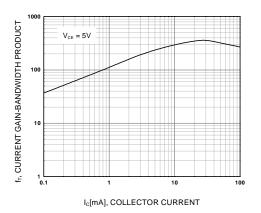
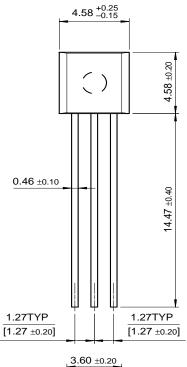
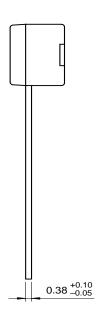


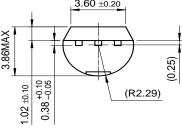
Figure 6. Current Gain Bandwidth Product

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Dimensions in Millimeters

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